ABSTRACT

An ether compound of formula (1) is provided wherein R^1 is H or C_{1-6} alkyl, R^2 is C_{1-6} alkyl, R^3 is H, C_{1-15} acyl or C_{1-15} alkoxycarbonyl which may be substituted with halogen atoms, k is 0 or 1, m is from 0 to 3, and n is from 3 to 6. The ether compound is polymerized to form a polymer having improved reactivity, robustness and substrate adhesion. A resist composition comprising the polymer as a base resin is sensitive to high-energy radiation, has excellent sensitivity, resolution, and etching resistance, and lends itself to micropatterning with electron beams or deep-UV.

